

CLAIM SUMMARY DOCUMENT

Claims 1-12 (Canceled)

Claim 13 (Original) A semiconductor light emitting device comprising:

a substrate:

gallium nitride type compound semiconductor layers having a light emitting portion,
said compound semiconductor layers including at least an n-type layer and a p-type layer,
said compound semiconductor layers being stacked on said substrate;

a buffer layer being interposed between said substrate and said semiconductor
layers;

wherein at least said substrate side of said buffer layer contains at least one kind of
element selected from a group consisting of In, P and As.

Claim 14 (Original) The semiconductor light emitting device according to Claim 13,
wherein said buffer layer has a low temperature buffer layer consists of $\text{In}_c\text{Ga}_{1-c}\text{N}$
($0 < c < 1$) or $\text{In}_d\text{Al}_e\text{Ga}_{1-d-e}\text{N}$ ($0 < d < 1$, $0 < e < 1$, $0 < d + e < 1$).

Claim 15 (Currently Amended) The semiconductor light emitting device according to
Claim 13, wherein said buffer layer has at least a low temperature buffer layer formed at
low temperature, said low temperature buffer layer consisting of $\text{GaN}_w\text{P}_{1-w}$ ($0 < w < 1$) or
 $\text{GaN}_v\text{As}_{1-v}$ ($0 < v < 1$).

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Claim ~~16~~ (Currently Amended) The semiconductor light emitting device according to Claim ~~13~~, wherein at least said substrate side of said buffer layer is a semiconductor layer where a minimum electric current ~~is difficult to flow~~ flows.

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Claim ~~17~~ (Currently Amended) The semiconductor light emitting device according to Claim ~~13~~, wherein all of said buffer layer includes at least one kind of element selected from a group consisting of In, P and As.

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Claim ~~18~~ (Currently Amended) The semiconductor light emitting device according to Claim ~~16~~, wherein at least said substrate side of said buffer layer consists of a semiconductor layer of high resistance.

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Claim ~~19~~ (Original) The semiconductor light emitting device according to Claim ~~13~~, wherein at least said substrate side of said buffer layer is conductive type semiconductor layer which is different from the semiconductor layer of conduction type stacked just over said buffer layer.

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Claim ~~20~~ (Currently Amended) The semiconductor light emitting device according to Claim ~~13~~, wherein said buffer layer consists of a p-type low temperature buffer layer formed at low temperature on the surface of said substrate and high temperature buffer layer formed at high temperature on said low temperature buffer layer with at least the surface side ~~is~~ made into an n—type; wherein on said high temperature buffer layer are

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formed sequentially an n—type clad layer, ~~and~~ active layer, a p—type clad layer, and p—type contact layer in that order; ~~wherein~~ wherein a p—side electrode is ~~formed~~ formed on said n—type clad layer or on a high temperature buffer layer exposed by etching.

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Claim 21 (Currently Amended) The semiconductor light emitting device according to Claim ~~20~~, wherein said low and high temperature buffer layer consists layers consists of GaN; wherein said n—type and p—type clad layers ~~respectively~~ respectively consist of $\text{Al}_k\text{Ga}_{1-k}\text{N}$ ($0 < k < 1$); wherein said active layer consists of $\text{Ga}_y\text{In}_{1-y}\text{N}$ ($0 < y \leq 1$) and wherein said p-type contact layer consists of GaN.

Claims 22-52 (Withdrawn)

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